

Product data sheet

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2kV HBM

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	350	mA
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C		-	2.2	2.8	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.





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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D
2	S	source	2 2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G G S 017aaa255

## 6. Ordering information

Table 3.     Ordering information								
Type number	Package							
	Name	Description	Version					
NX7002BKM	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883					

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
NX7002BKM	WZ

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	350	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	200	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	0.9	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	350	mW
			[1]	-	680	mW
		T <sub>sp</sub> = 25 °C		-	3100	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	200	mA

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

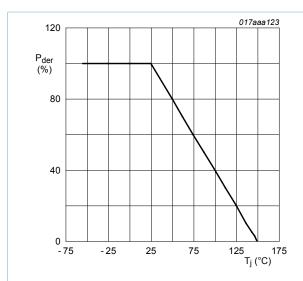
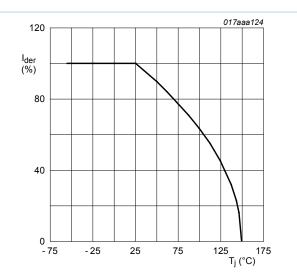


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

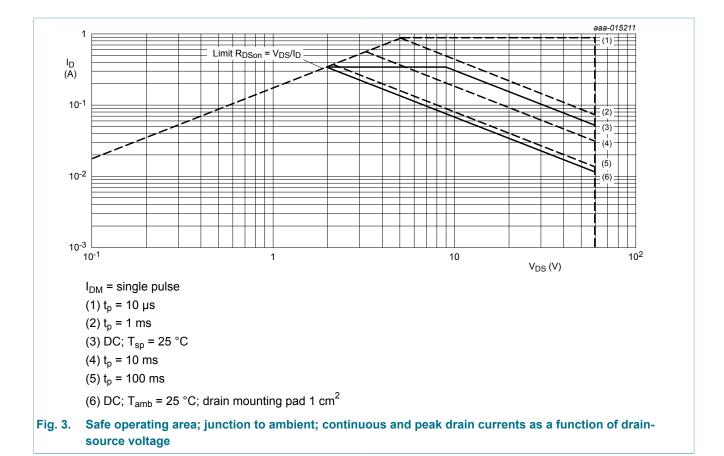




$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

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# 9. Thermal characteristics

Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	314	360	K/W
			[2]	-	159	180	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	35	40	K/W

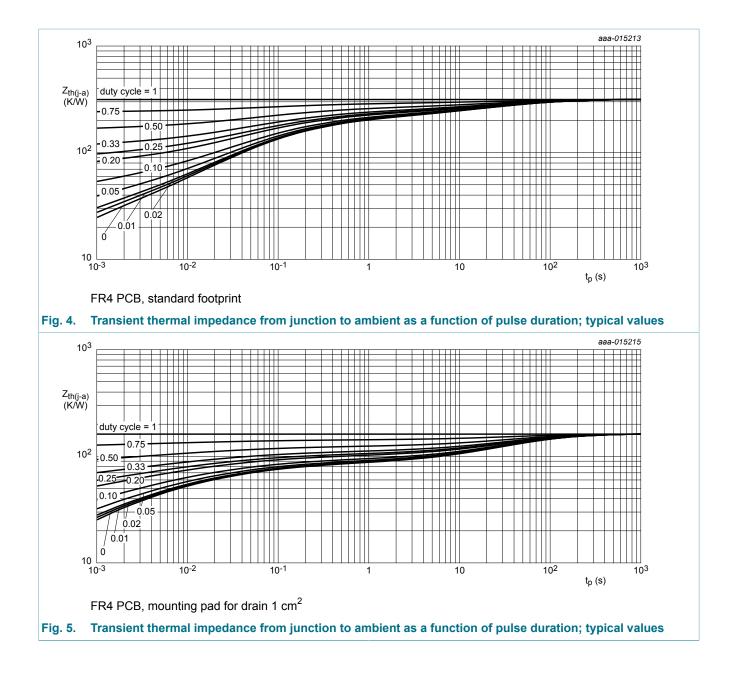
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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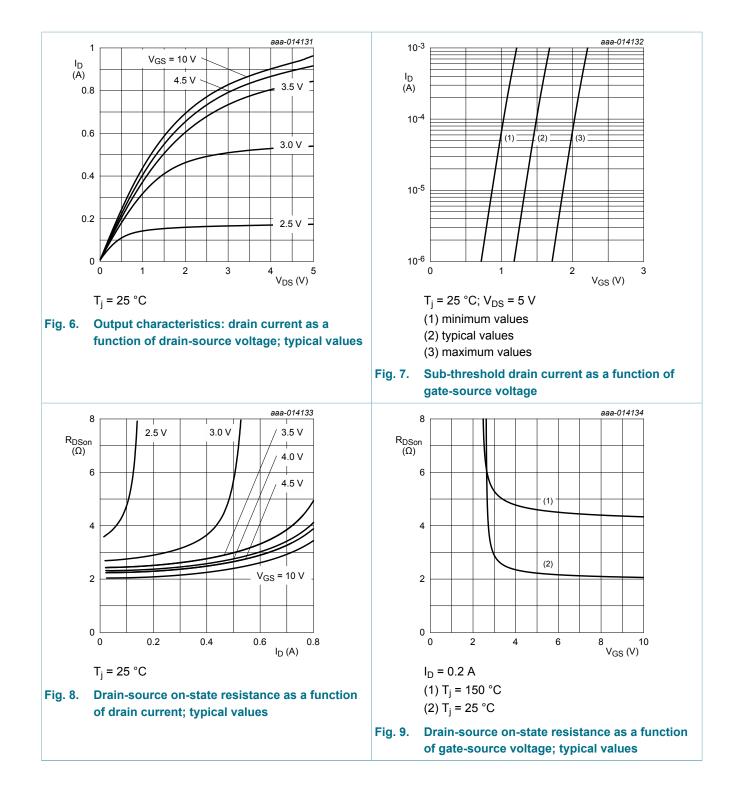
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1.1	1.6	2.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	10	μA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		$V_{GS}$ = 5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	0.3	μA
		V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.3	μA
R <sub>DSon</sub> drain-source or resistance	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.2	2.8	Ω
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 150 °C	-	4.5	5.7	Ω
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.5	3.2	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	600	-	mS
R <sub>G</sub>	internal gate resistance (AC)	f = 2.5 MHz	-	2.5	-	Ω
Dynamic ch	aracteristics	· · · ·	1	1		,
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	1	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.18	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	23.6	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	4.7	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	4.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	6.9	-	ns
t <sub>f</sub>	fall time		-	2.9	-	ns
Source-drai	in diode	· · ·	I			,
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 200 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.87	1.2	V

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#### 60 V, N-channel Trench MOSFET

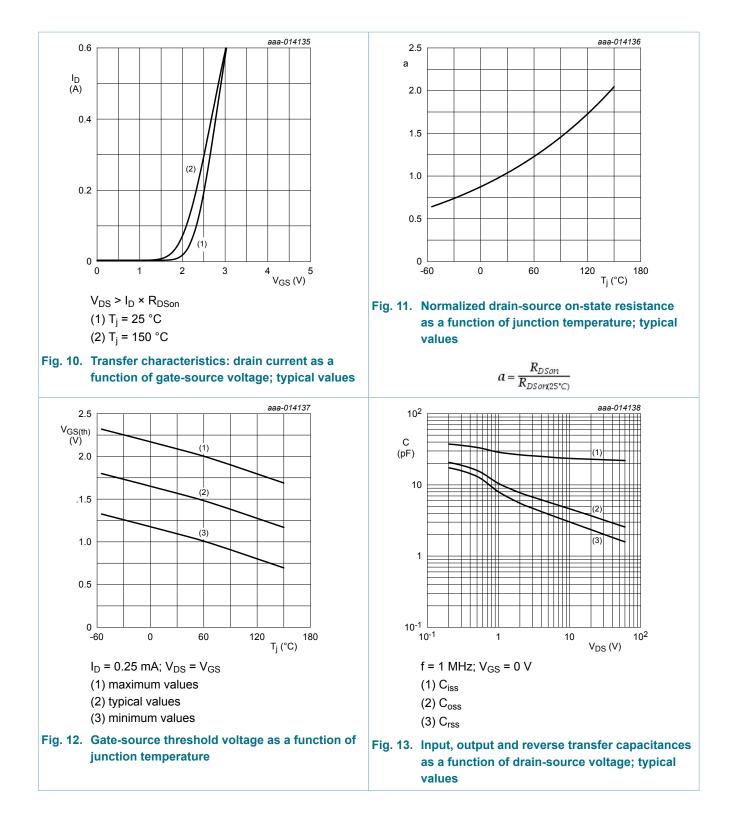


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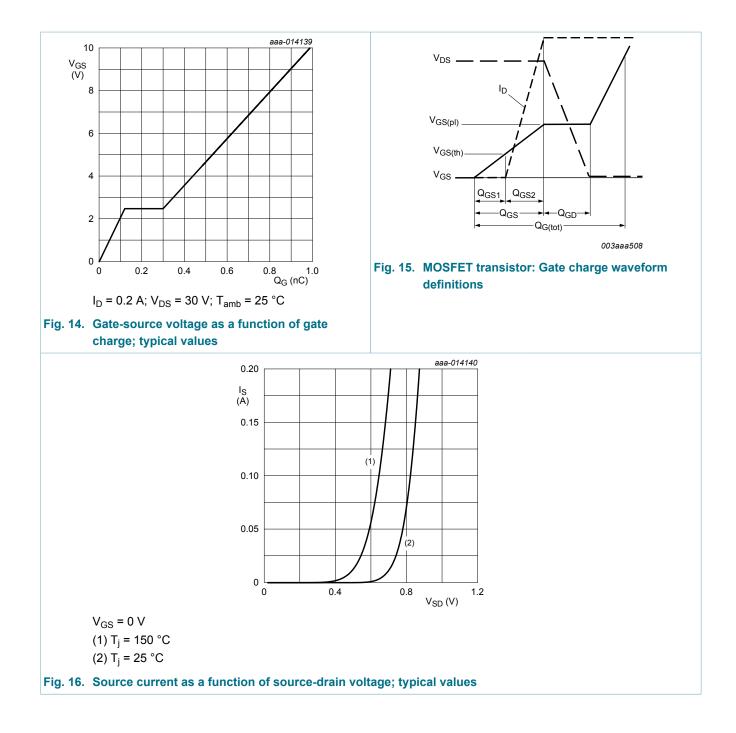


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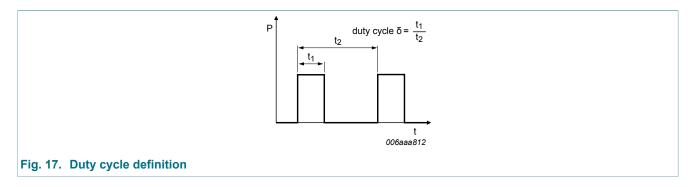
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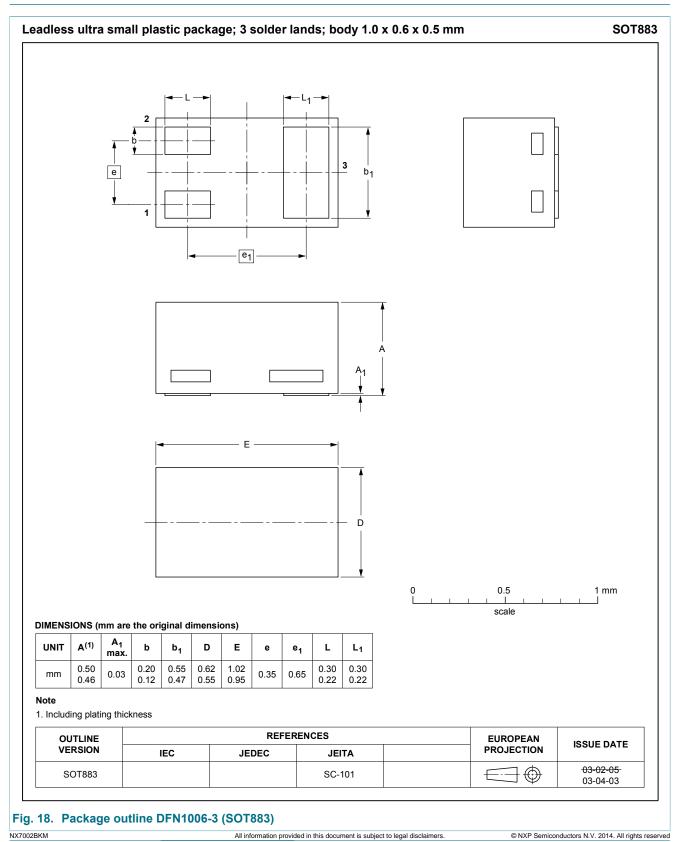
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### 11. Test information



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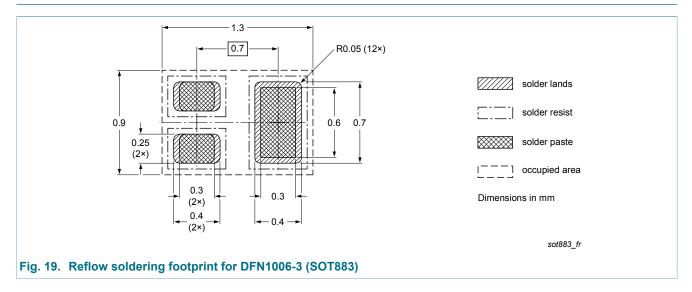
### 12. Package outline



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### 13. Soldering



## 14. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002BKM v.2	20141203	Product data sheet	-	NX7002BKM v.1
Modification:	Figure 3 updated			
NX7002BKM v.1	20141001	Product data sheet	-	-

#### 60 V, N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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